

10035503-102504

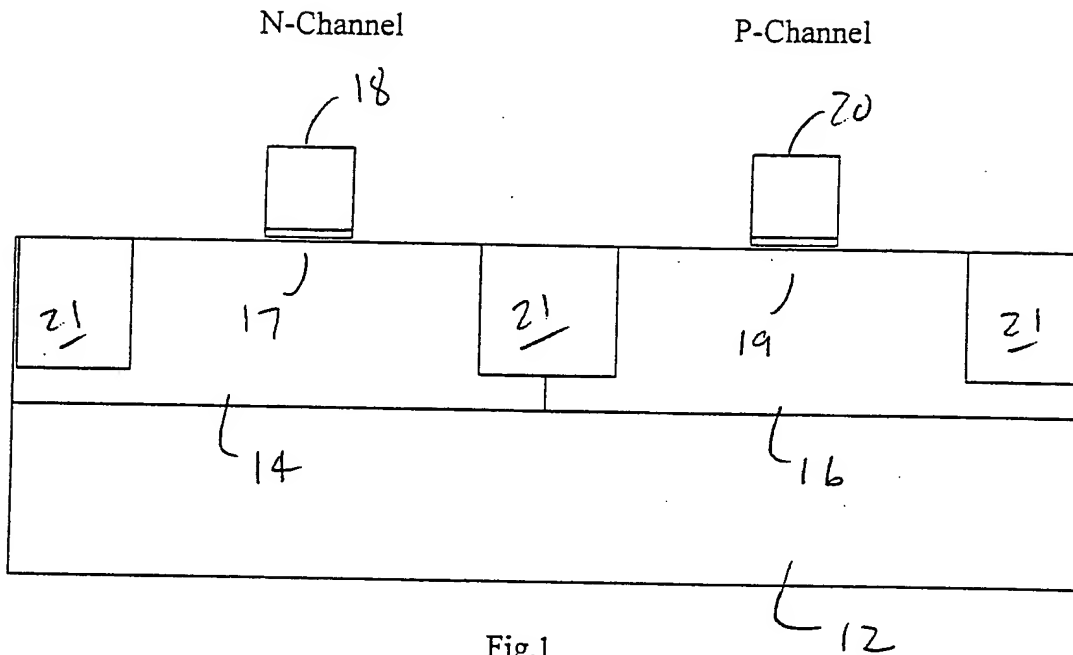


Fig.1

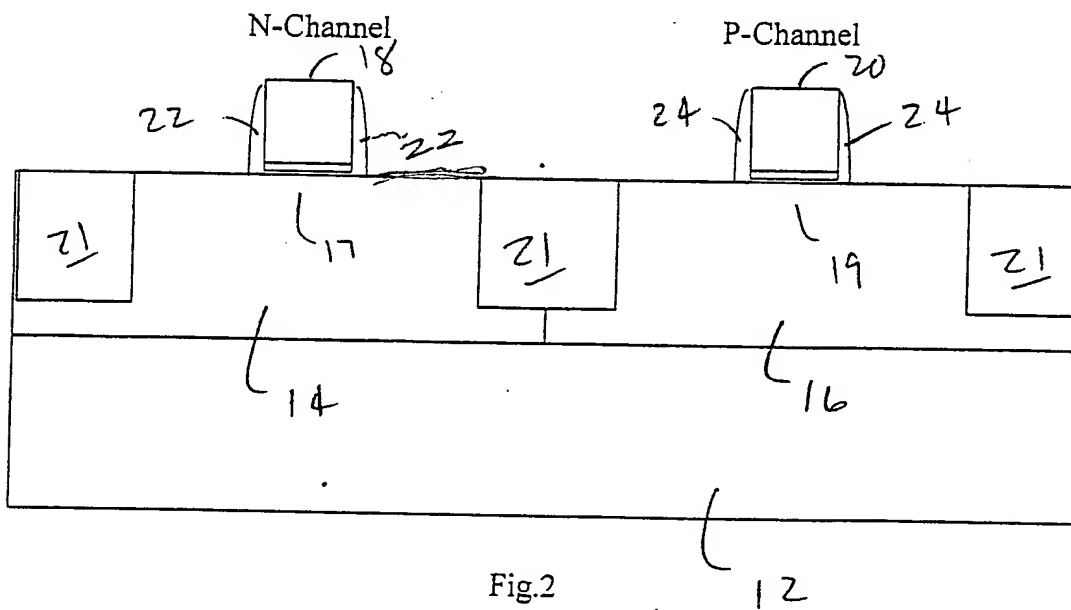
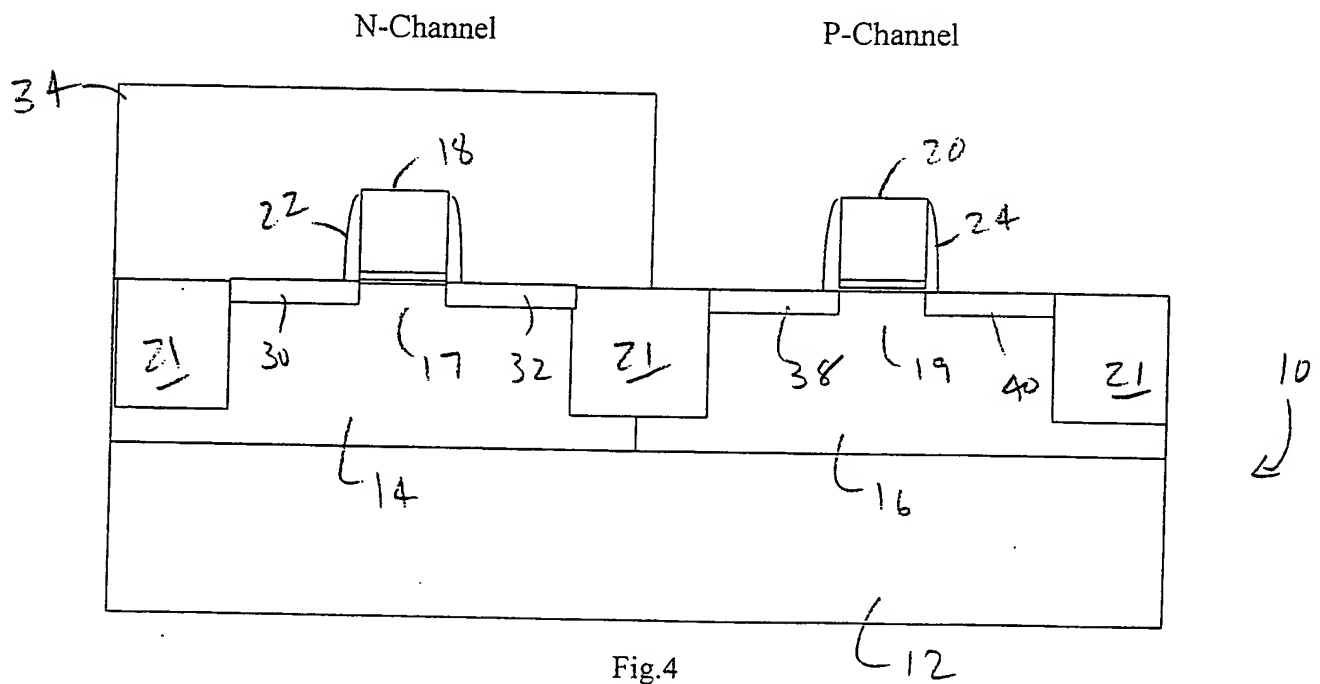
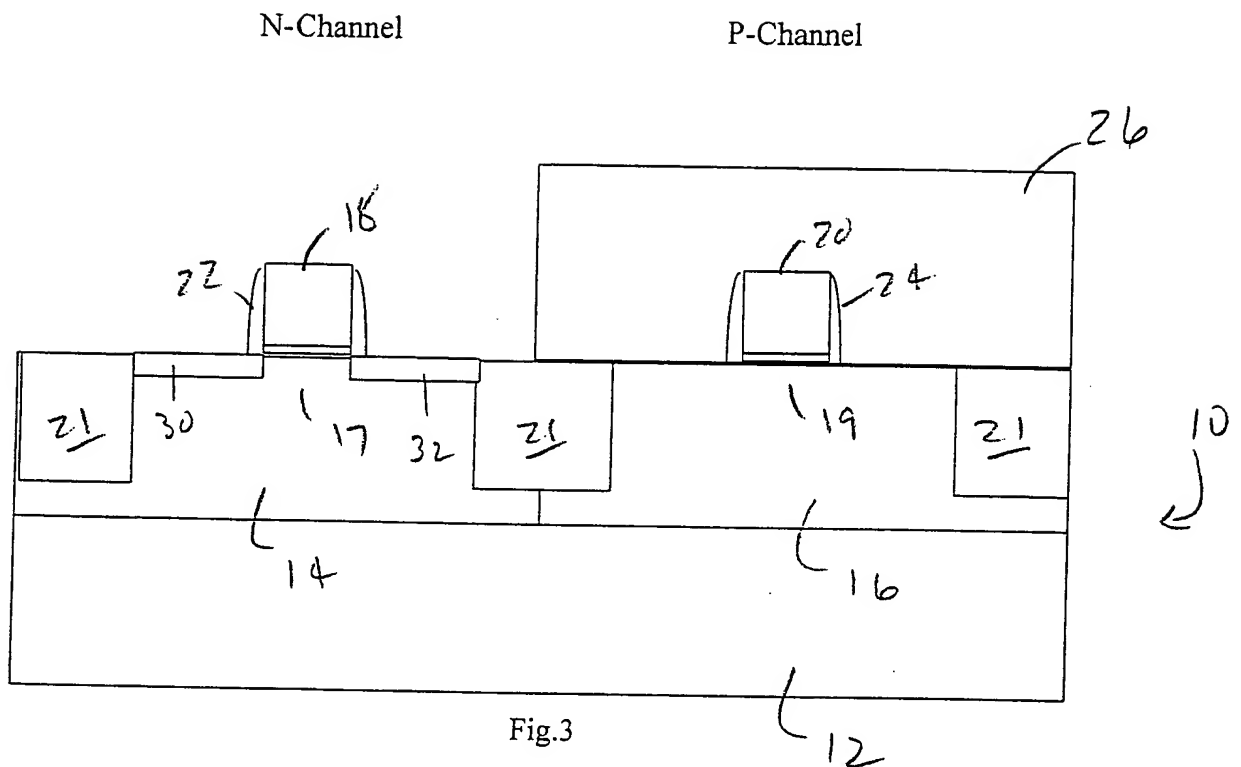


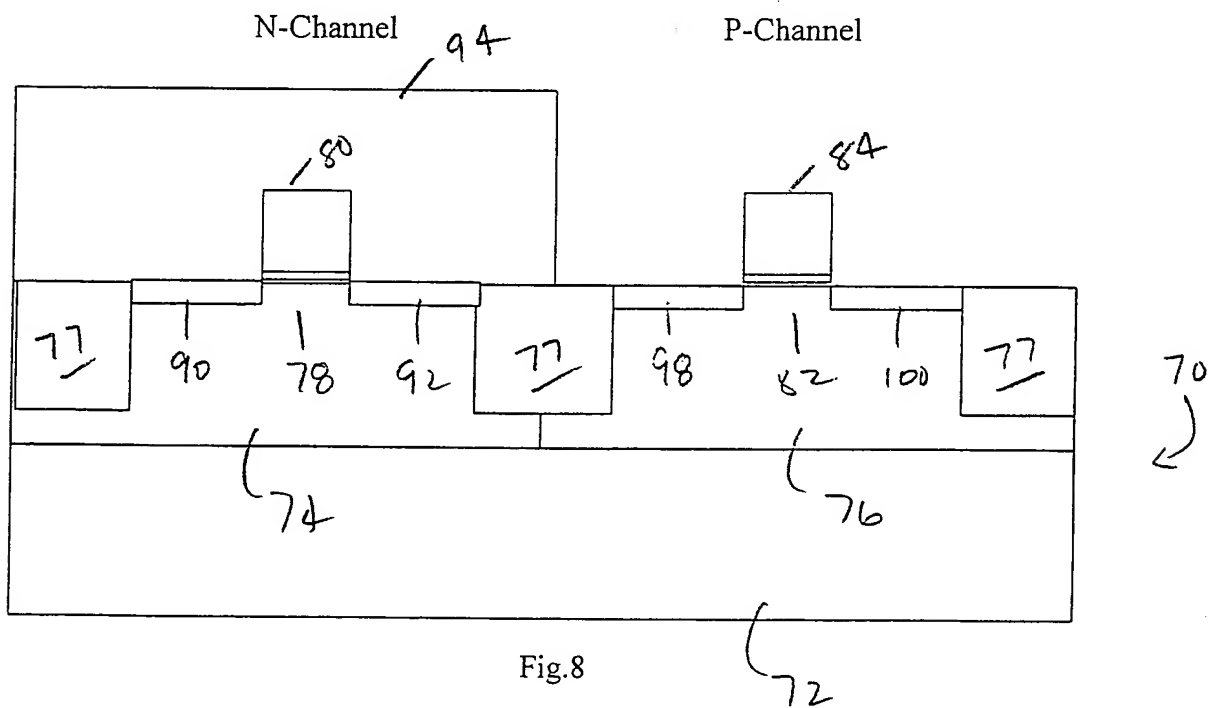
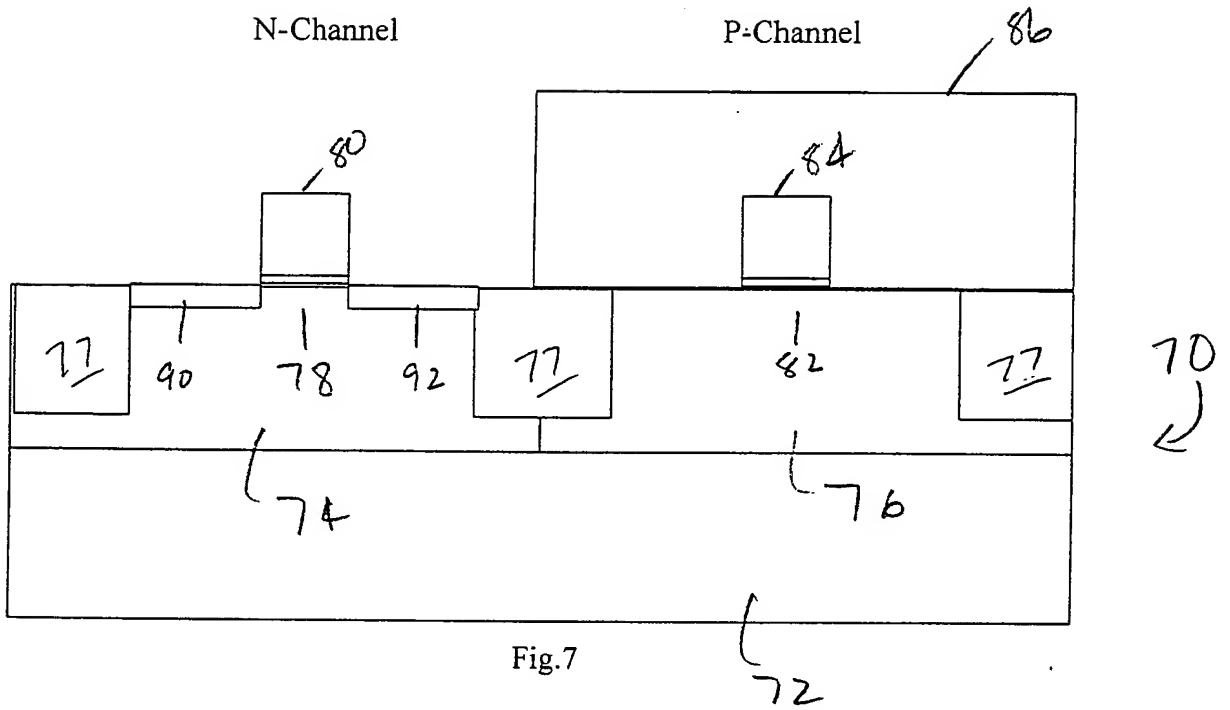
Fig.2



[illegible]

A cross-sectional view of a semiconductor device. The top surface is divided into two main regions: "N-Channel" on the left and "P-Channel" on the right. The device consists of a substrate (12) with a base layer (14). On the N-Channel side, there are three gate structures (42) and one central gate structure (44). The gate structures are labeled 42, 50, 52, 40, 54, 56, and 58. The central gate structure (44) is labeled 20. The regions between the gates are labeled 30, 17, 32, 38, 18, and 40. The regions on the far left and right are labeled 21. The regions between the gates are labeled 22, 42, 44, and 24. The regions between the gates are labeled 18 and 20. The regions between the gates are labeled 14 and 16.

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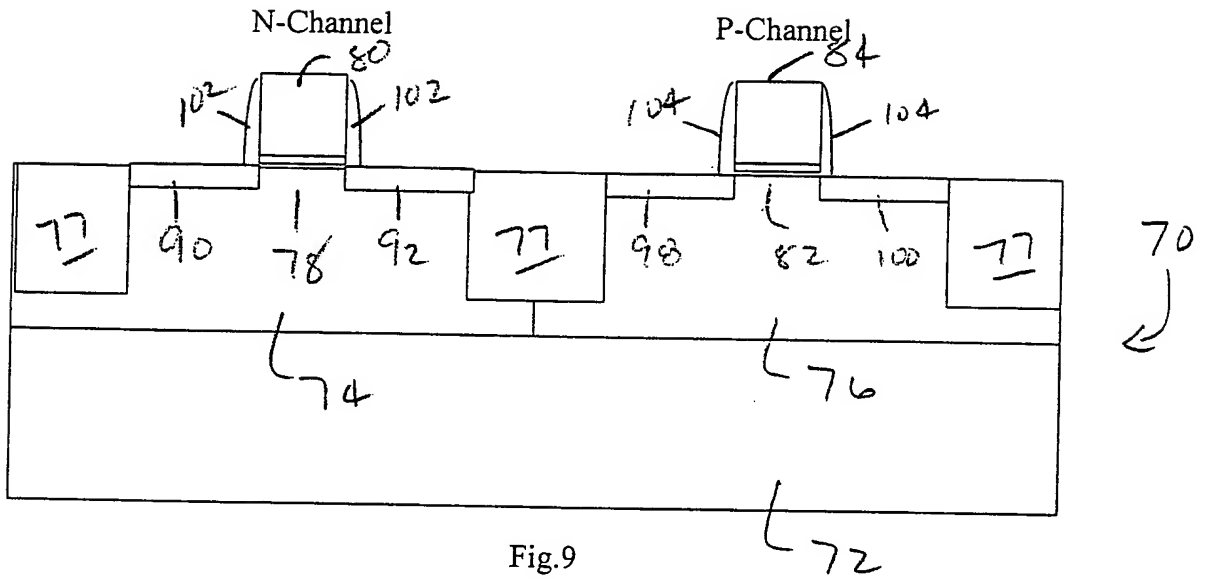


Fig. 9

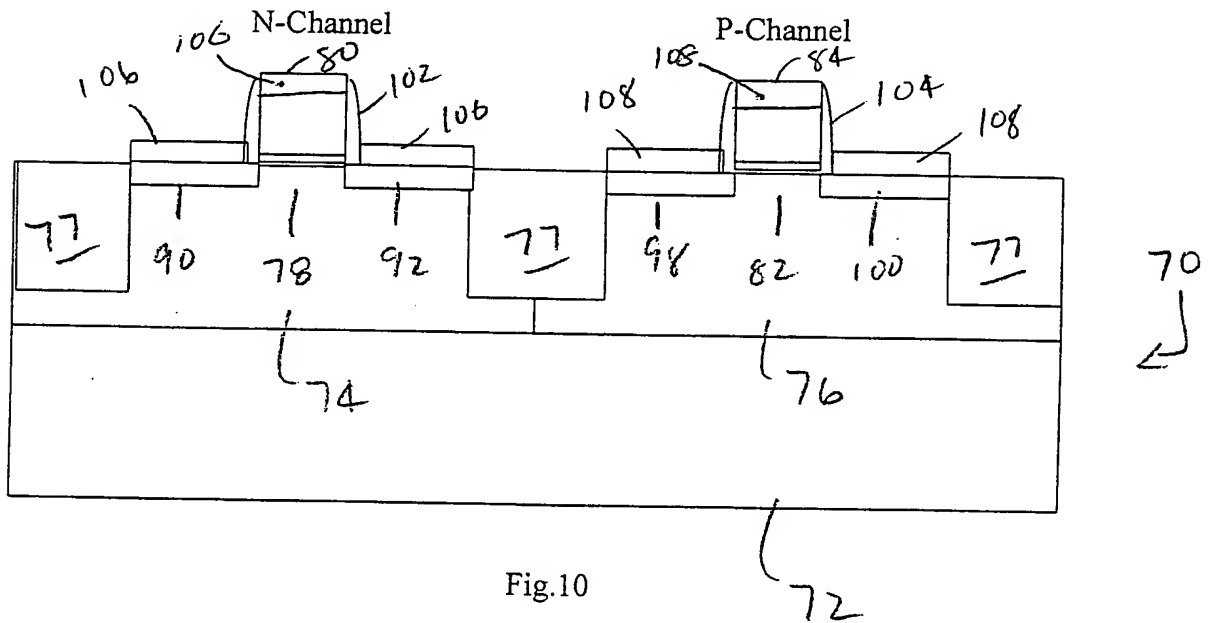


Fig. 10

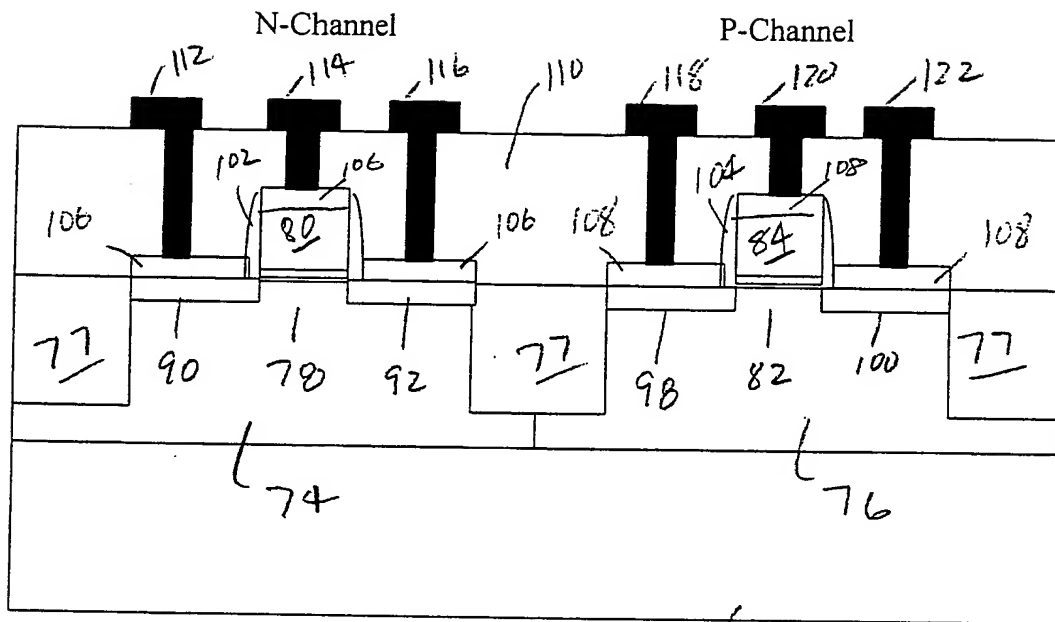


Fig.11

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